



General Description

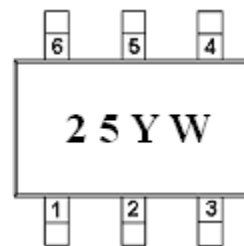
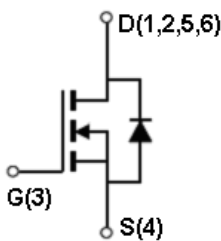
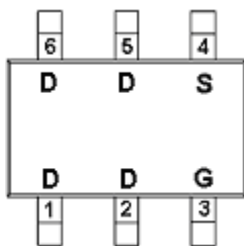
AFP3425, P-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.

These devices are particularly suited for low voltage power management, such as smart phone and notebook computer and other battery powered circuits, and low in-line power loss are needed in commercial industrial surface mount applications.

Features

- -20V/-4.0A, $R_{DS(ON)}=56m\Omega@V_{GS}=4.5V$
- -20V/-3.2A, $R_{DS(ON)}=70m\Omega@V_{GS}=2.5V$
- -20V/-2.8A, $R_{DS(ON)}=96m\Omega@V_{GS}=1.8V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- TSOP-6 package design

Pin Description (TSOP-6)



Application

- Portable Equipment
- Battery Powered System
- Net Working System

Pin Define

Pin	Symbol	Description
1	D	Drain
2	D	Drain
3	G	Gate
4	S	Source
5	D	Drain
6	D	Drain

Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFP3425TS6RG	25YW	TSOP-6	Tape & Reel	3000 EA

- ※ 25 parts code
- ※ Y year code (0 ~ 9)
- ※ W week code (A ~ Z = 1 ~ 26 / a ~ z = 27 ~ 52)
- ※ AFP3425TS6RG : 7" Tape & Reel ; Pb- Free ; Halogen- Free



Absolute Maximum Ratings

(T_A=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V _{DSS}	-20	V
Gate –Source Voltage	V _{GSS}	±12	V
Continuous Drain Current(T _J =150°C)	I _D	T _A =25°C	-4.0
		T _A =70°C	-2.8
Pulsed Drain Current	I _{DM}	-12	A
Continuous Source Current(Diode Conduction)	I _S	-1.6	A
Power Dissipation	P _D	T _A =25°C	2.0
		T _A =70°C	1.3
Operating Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{STG}	-55/150	°C
Thermal Resistance-Junction to Ambient	R _{θJA}	120	°C/W

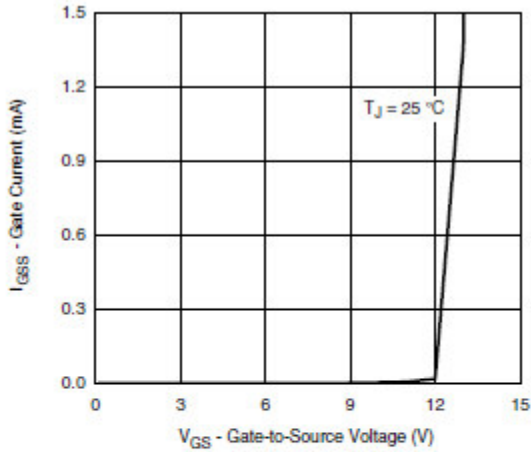
Electrical Characteristics

(T_A=25°C Unless otherwise noted)

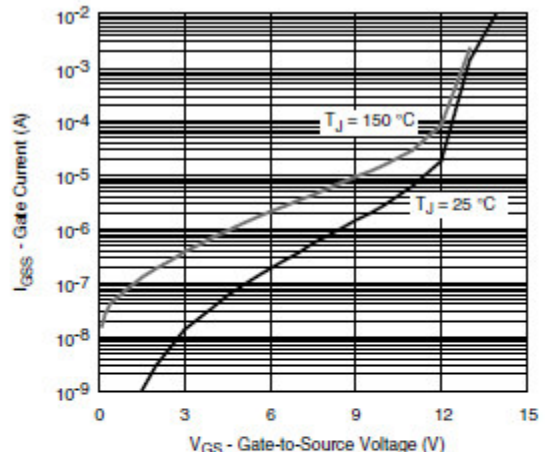
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =-250uA	-20			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250uA	-0.4		-0.8	
Gate Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±12V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-16V, V _{GS} =0V			-1	uA
		V _{DS} =-16V, V _{GS} =0V T _J =85°C			-10	
On-State Drain Current	I _{D(on)}	V _{DS} ≥ -5V, V _{GS} =-4.5V	-6			A
		V _{DS} ≥ -5V, V _{GS} =-2.5V	-4			
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =-4.5V, I _D =-4.0A		50	56	mΩ
		V _{GS} =-2.5V, I _D =-3.2A		60	70	
		V _{GS} =-1.8V, I _D =-2.8A		80	96	
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-3.6A		10		S
Diode Forward Voltage	V _{SD}	I _S =-1.6A, V _{GS} =0V		-0.85	-1.2	V
Dynamic						
Total Gate Charge	Q _g	V _{DS} =-10V, V _{GS} =-4.5V I _D ≡-4.0A		8.0	12	nC
Gate-Source Charge	Q _{gs}			0.9		
Gate-Drain Charge	Q _{gd}			3.0		
Input Capacitance	C _{iss}	V _{DS} =-10V, V _{GS} =0V f=1MHz		780		pF
Output Capacitance	C _{oss}			115		
Reverse Transfer Capacitance	C _{rss}			55		
Turn-On Time	t _{d(on)}	V _{DD} =-10V, R _L =2.3Ω I _D ≡-4.0A, V _{GEN} =-4.5V R _G =1Ω		0.2	0.3	us
	t _r			1.0	1.5	
Turn-Off Time	t _{d(off)}			4.0	6.0	
	t _f			2.0	3.0	



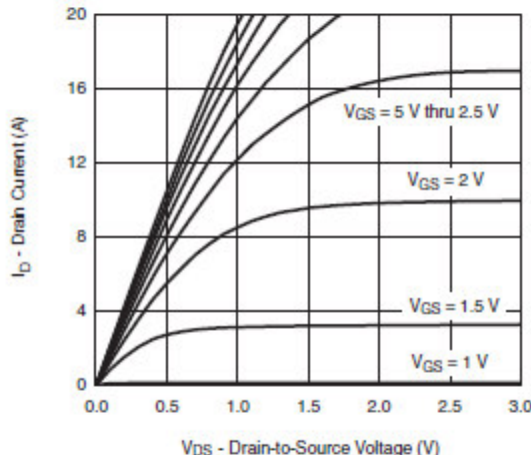
Typical Characteristics



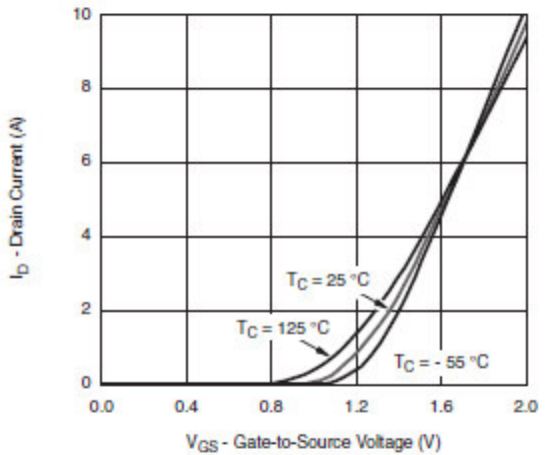
Gate Current vs. Gate-Source Voltage



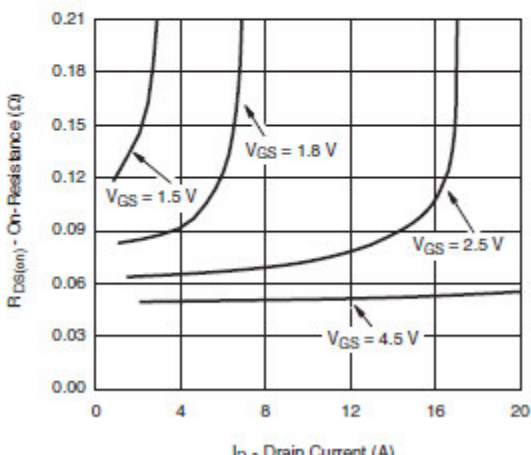
Gate Current vs. Gate-Source Voltage



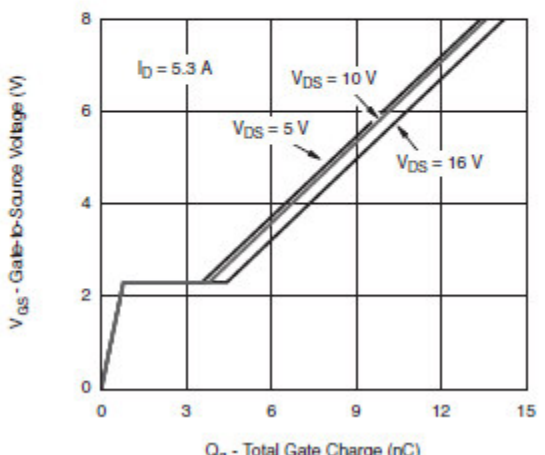
Output Characteristics



Transfer Characteristics



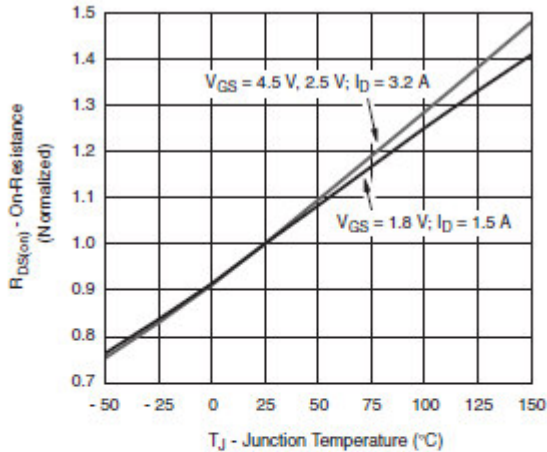
On-Resistance vs. Drain Current



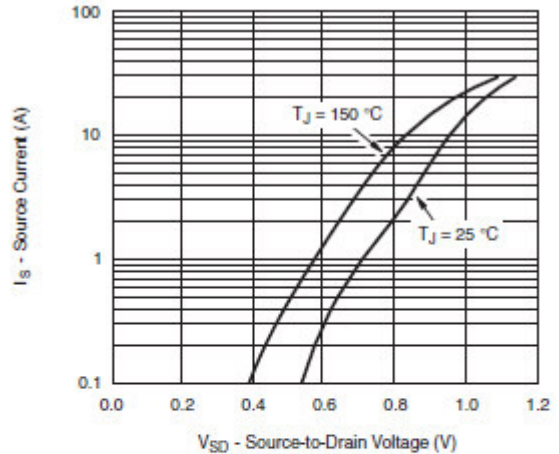
Gate Charge



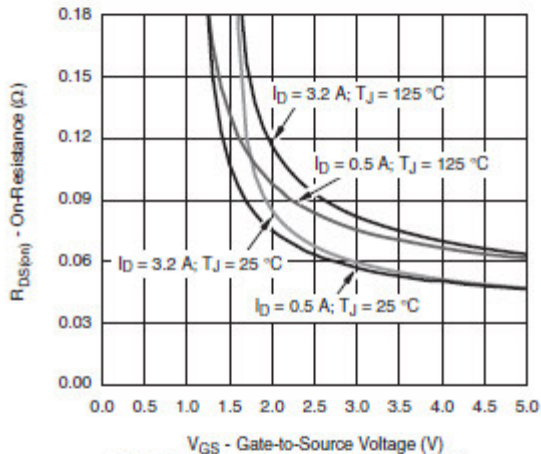
Typical Characteristics



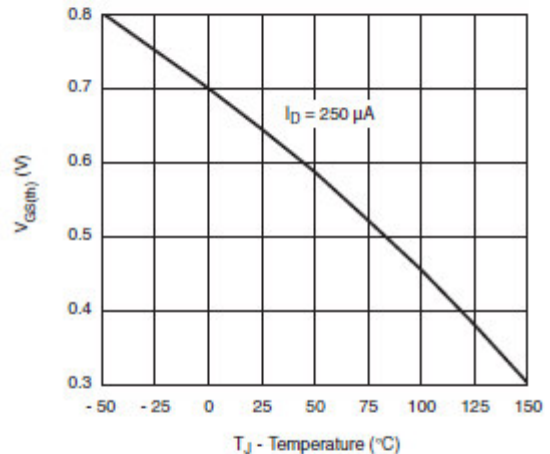
On-Resistance vs. Junction Temperature



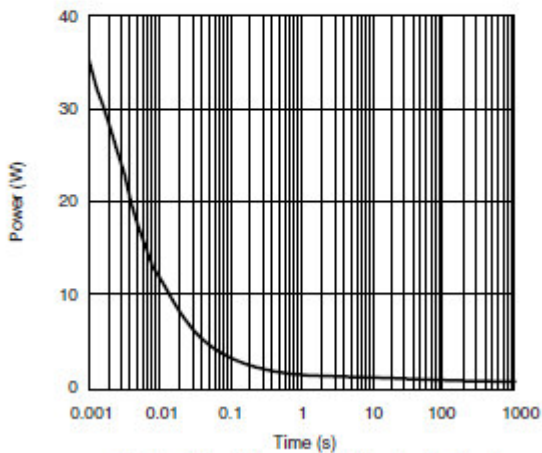
Source-Drain Diode Forward Voltage



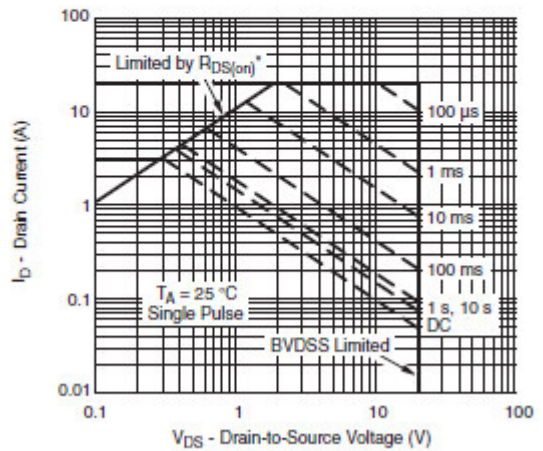
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power, Junction-to-Ambient

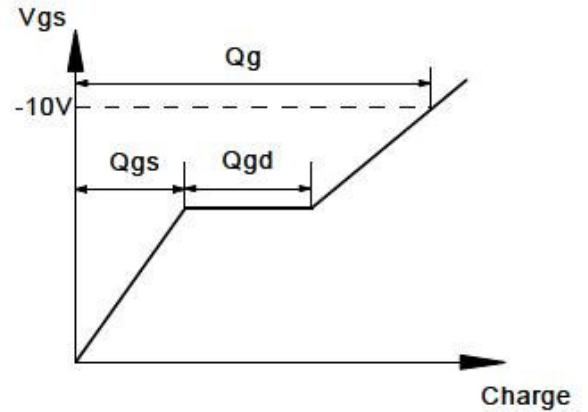
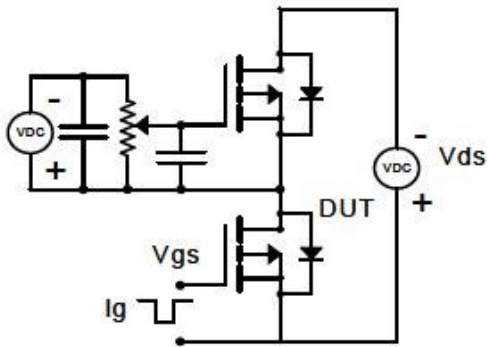


* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified
Safe Operating Area, Junction-to-Ambient

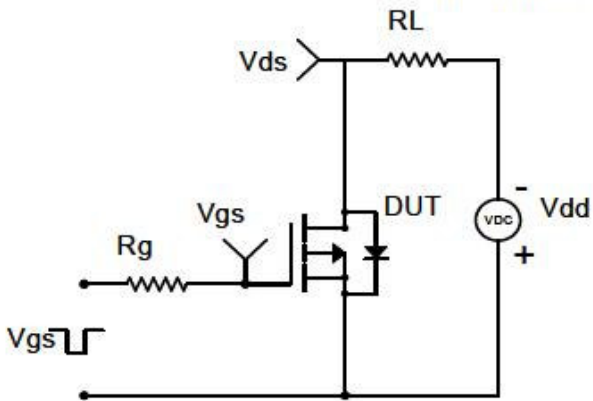


Typical Characteristics

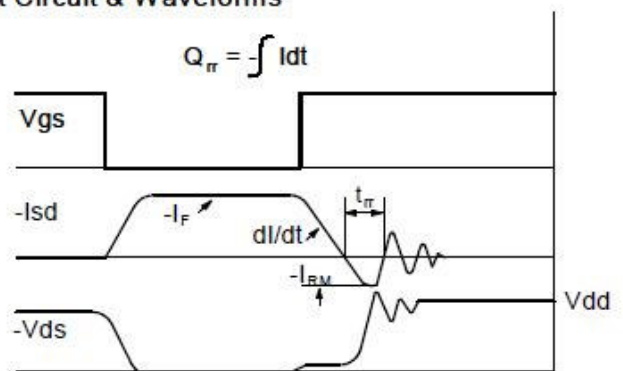
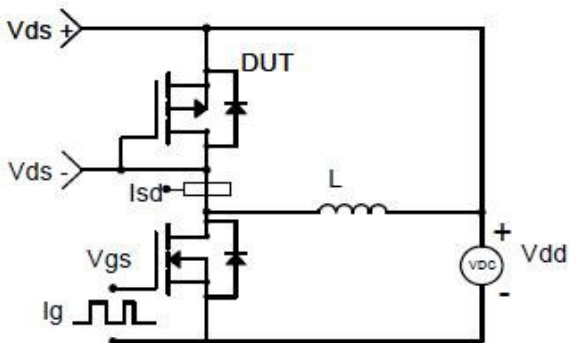
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

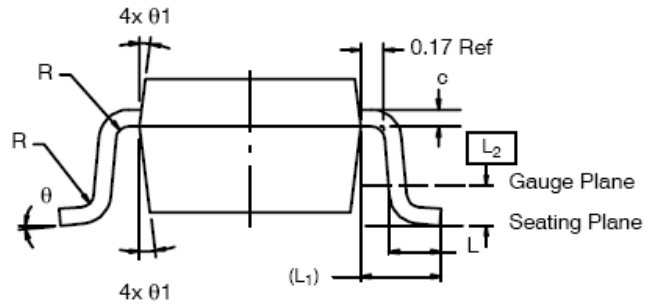
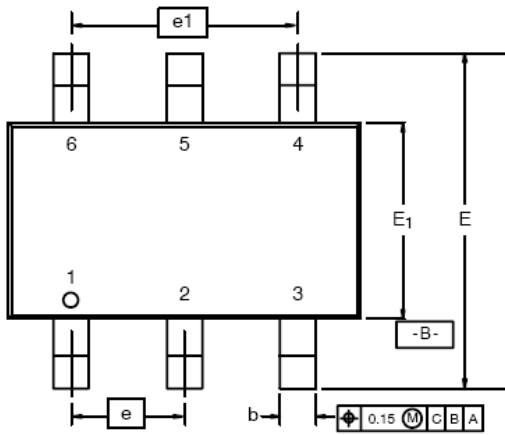


Diode Recovery Test Circuit & Waveforms





Package Information (TSOP-6)



Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.91	-	1.10	0.036	-	0.043
A ₁	0.01	-	0.10	0.0004	-	0.004
A ₂	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.96	0.106	0.112	0.117
E ₁	1.55	1.65	1.70	0.061	0.065	0.067
e	1.00 BSC			0.0394 BSC		
e ₁	1.90	2.00	2.10	0.075	0.080	0.085
L	0.35	-	0.50	0.014	-	0.020
L ₁	0.60 Ref			0.024 Ref		
L ₂	0.25 BSC			0.010 BSC		
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
θ ₁	7° Nom			7° Nom		

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